

# Sensores Integrados

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**Universidade do Minho**  
**Escola de Engenharia**  
Departamento de Electrónica Industrial



# Review previous classes

- Piezoresistivity
- Capacitive techniques
- Seebeck effect
- Peltier effect
- Hall effect
- Magnetoresistive
- PT100
- P-N Junction temperature sensors
- Radiação
- Reflexão interna total
- Absorvência
- Fluorescência
- Lminescência
- SPR

# Resumo

1. Sensores de pressão
2. Sensores de fluxo
3. Sensores óticos

# 1. Pressure Sensors



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# Pressure Sensors



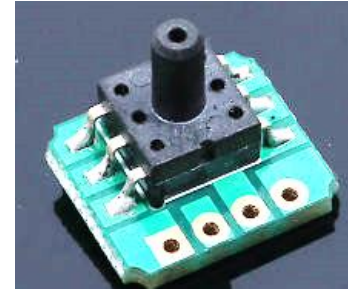
## ■ Introduction

- The application of MEMS to the measurement of pressure is a mature application of micromachined silicon sensors, and devices have been around for more than 40 years.
- The suitability of MEMS to mass-produced miniature high-performance sensors at low-cost has opened up a wide range of applications:
  - *Automotive*
  - *Industrial process control*
  - *Hydraulic systems*
  - *Microphones*
- Pressure is defined as a force per unit area, and the standard SI unit of pressure is N/m<sup>2</sup> or Pascal (Pa). 1 Pa = 1 N/m<sup>2</sup>

Units of Pressure and Conversion Factor to Pa (to Two Decimal Places)

Unit	Symbol	No. of Pascals
Bar	bar	$1 \times 10^5$
Atmosphere	atm	$1.01325 \times 10^5$

# Pressure Sensors



## ■ Pressure sensor types

- Absolute pressure sensors

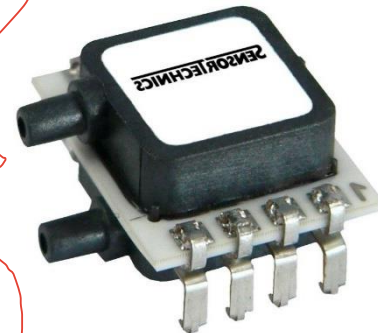
- Devices that measure **relative to a vacuum** and therefore must have a reference vacuum encapsulated within the sensor. Atmospheric pressure is measured using absolute sensors.

- Gauge pressure sensors

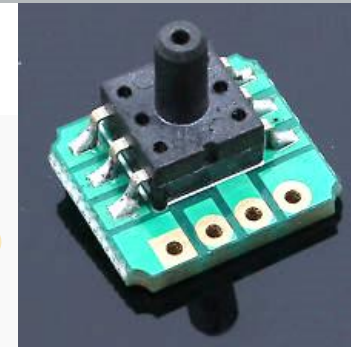
- Devices that measure **relative to atmospheric pressure**, and therefore, part of the sensor must be vented to the ambient atmosphere.

- Differential pressure sensors

- Devices that measure the **difference between two pressure measurands**. The design of differential pressure sensors often represents the greatest challenge since two pressures must be applied to the mechanical structure.

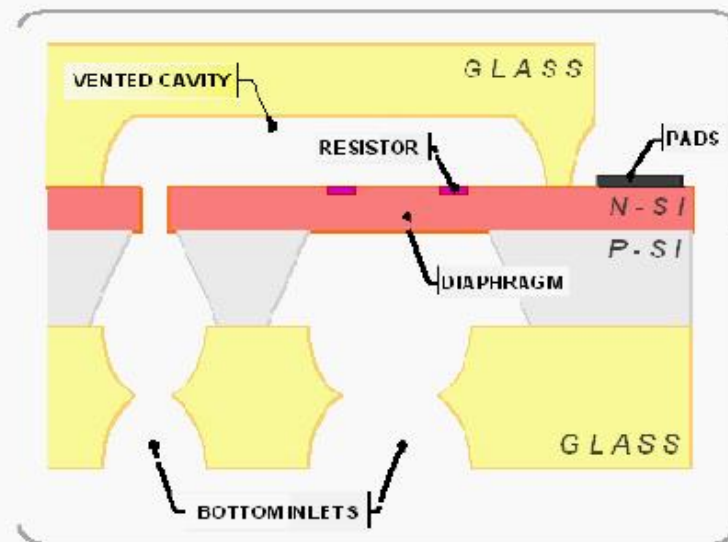
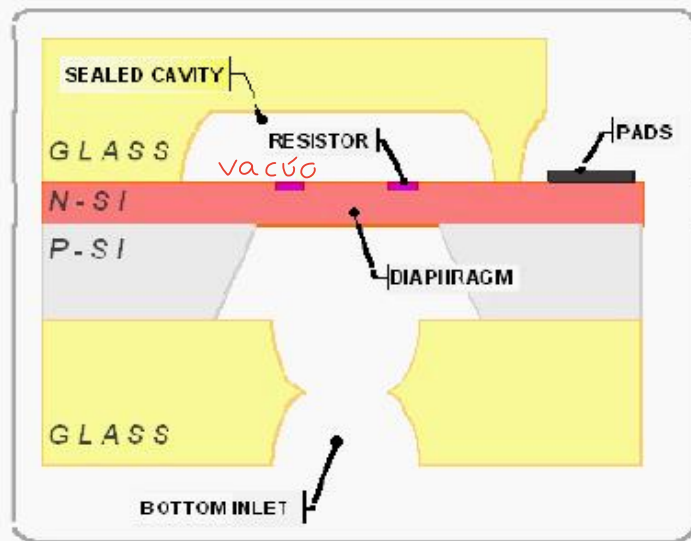


# Pressure Sensors



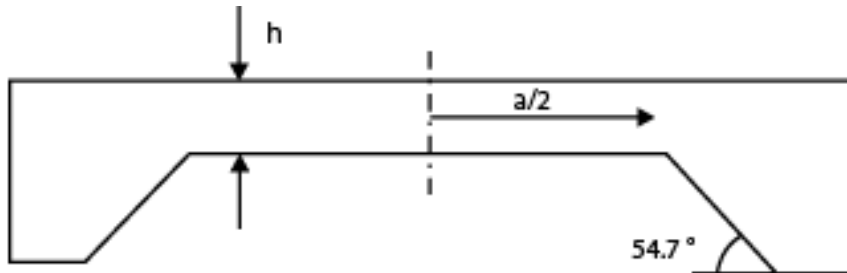
Absolute Pressure Sensor

Relative Pressure Sensor

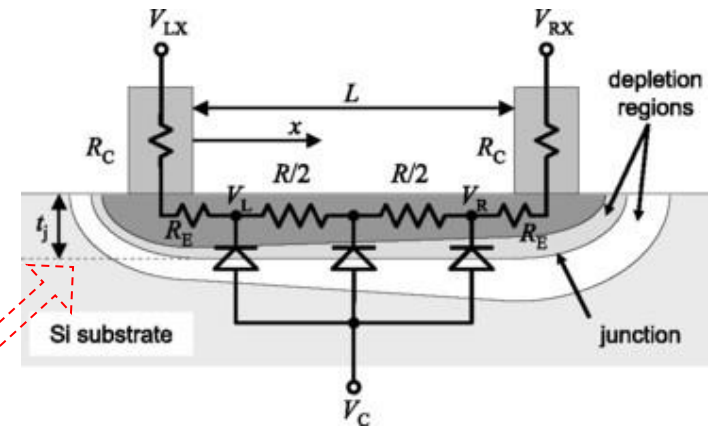
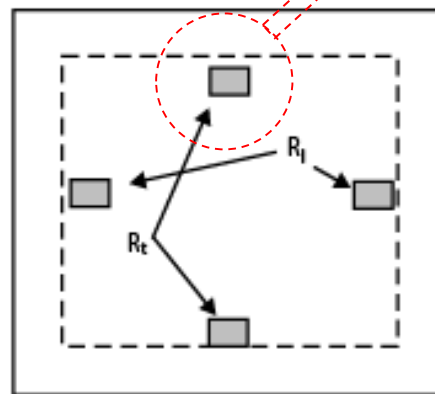
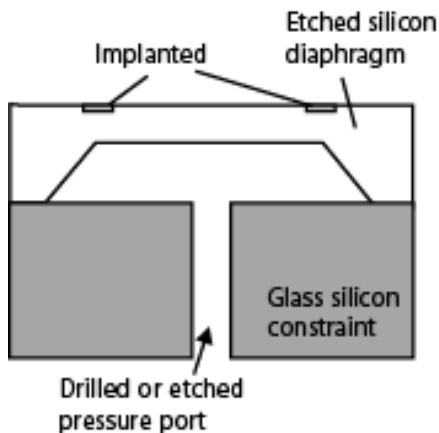


# Pressure sensors

## ■ Micromachined Silicon Diaphragms



- Fabricated using anisotropic wet etching.



Diffused resistor, in the piezoresistive sensing element

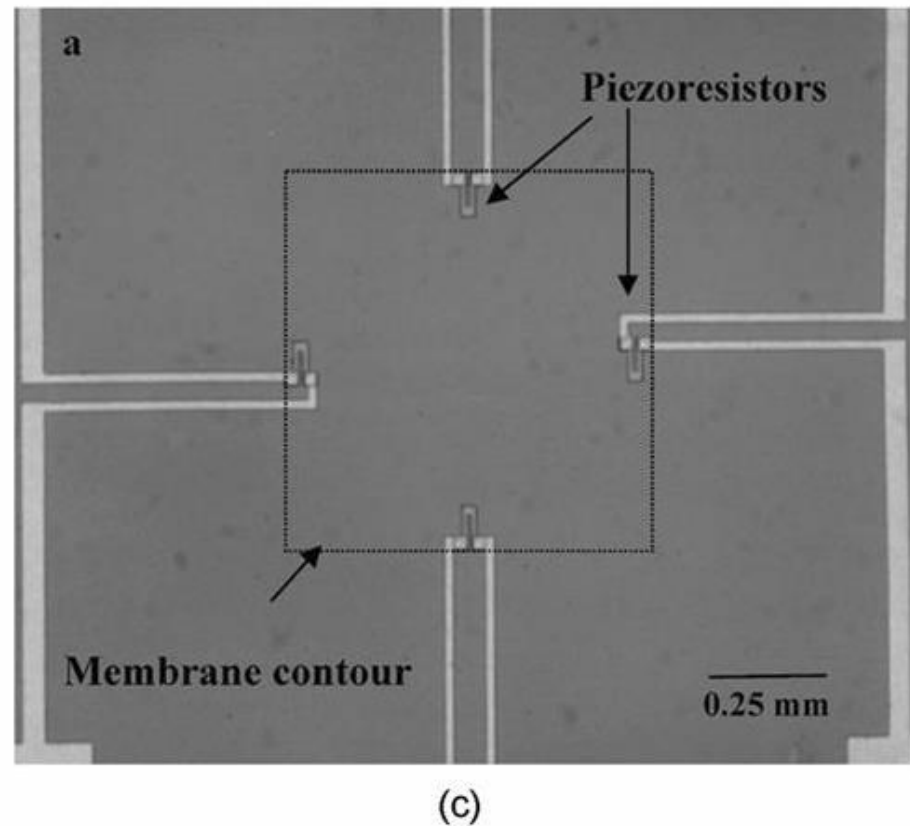
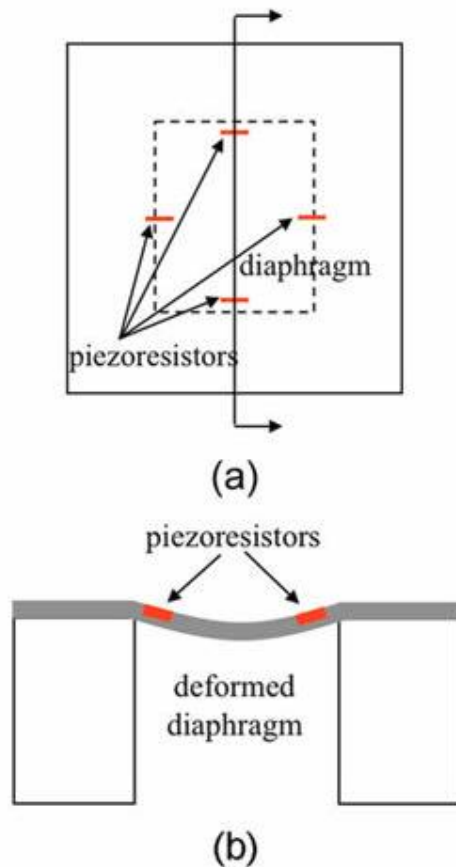
The piezoresistive nature of silicon makes the use of diffused or implanted resistors an obvious and straightforward technique for measuring the strain in micromachined silicon diaphragm.



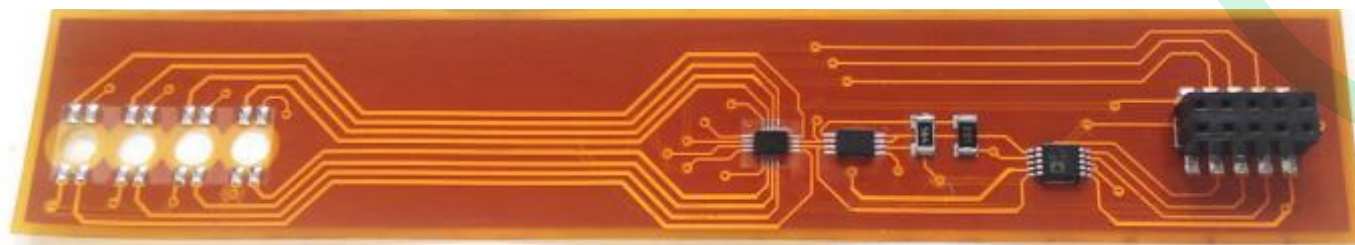
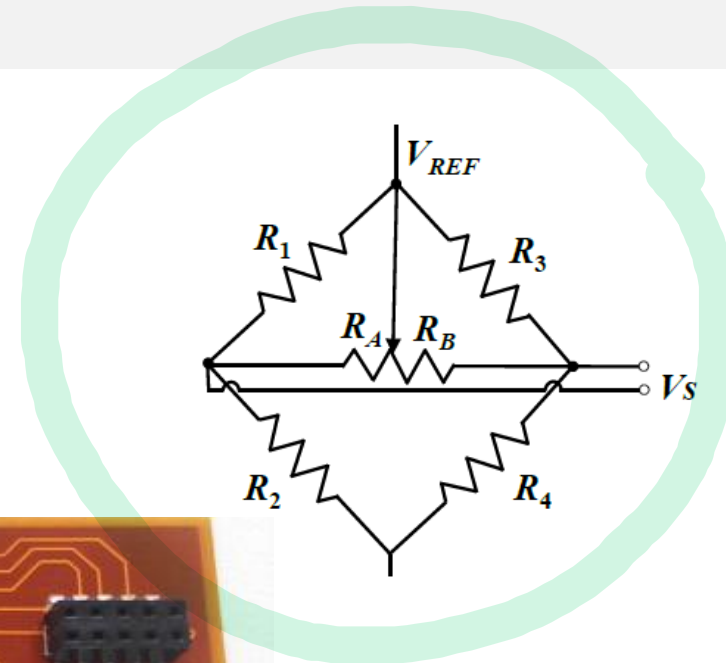
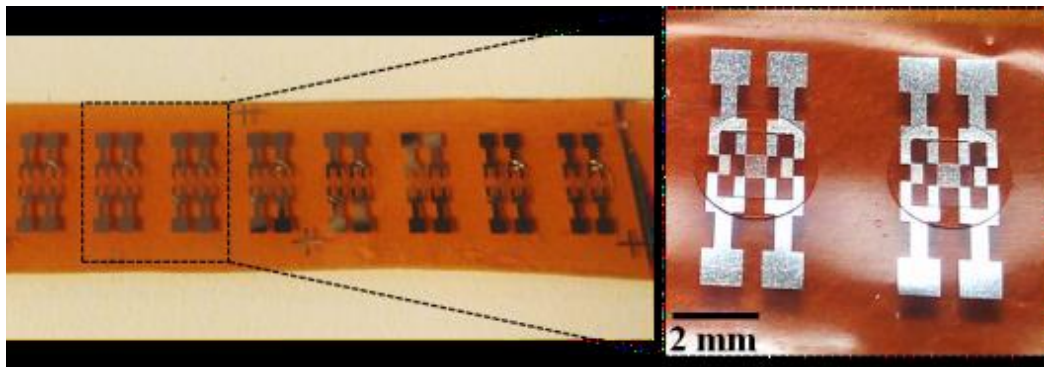
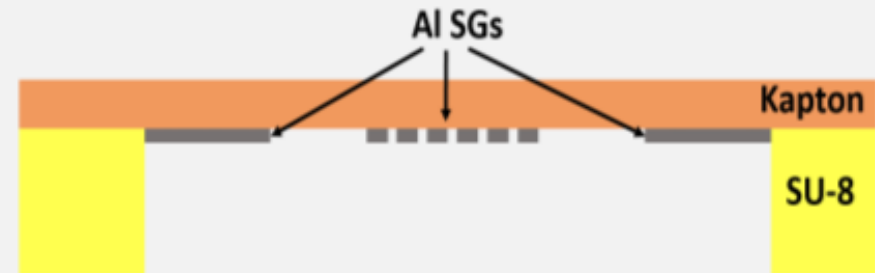
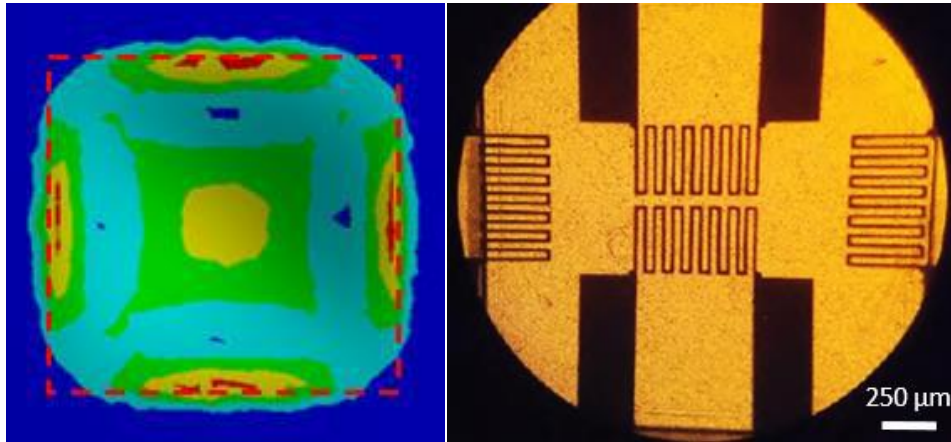
# Pressure Sensors



## ■ Piezoresistive Pressure Sensors



# Other example: Aluminium strain Gauges (SG) in a flexible Kapton substrate



# Pressure Sensors



## ■ Capacitive Pressure Sensors

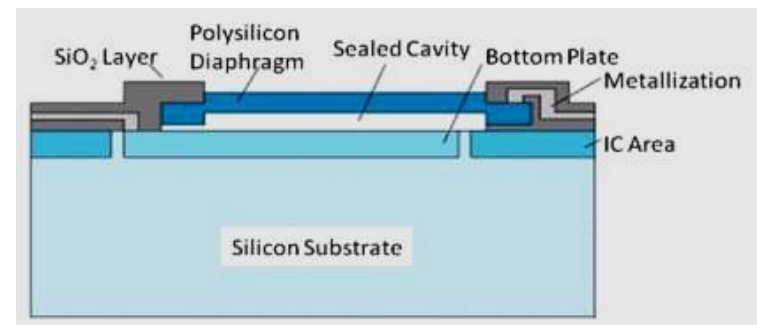
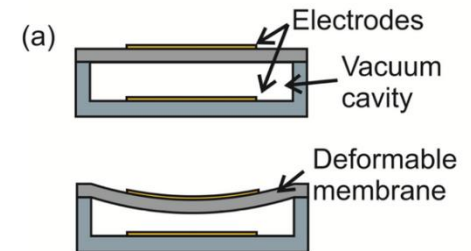
- Capacitive pressure sensors are typically based upon a parallel plate arrangement, with a fixed electrode and the other one movable. As the flexible electrode deflects under applied pressure, the gap between electrodes decreases and the capacitance increases.

- **Advantages:**

- High sensitivity to pressure.
- Low power consumption.
- Low temperature cross-sensitivity.

- **Drawbacks:**

- Nonlinear output of the sensor
- Electronics complexity (compared with the resistive bridge)

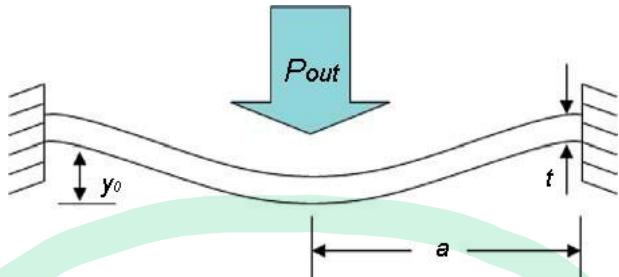


# Pressure Sensors - Capacitive

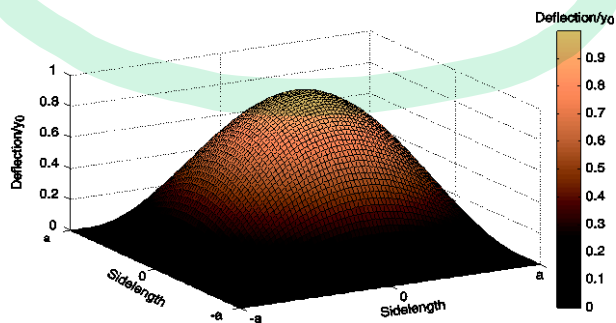
## Analytical model

### Mechanical domain

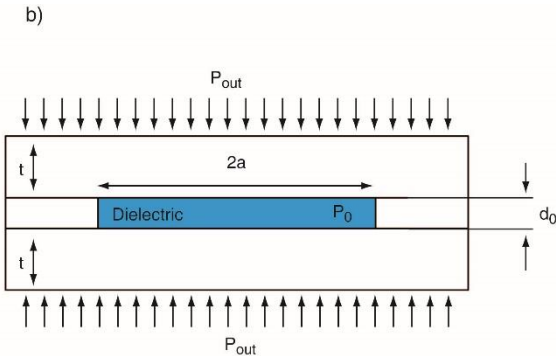
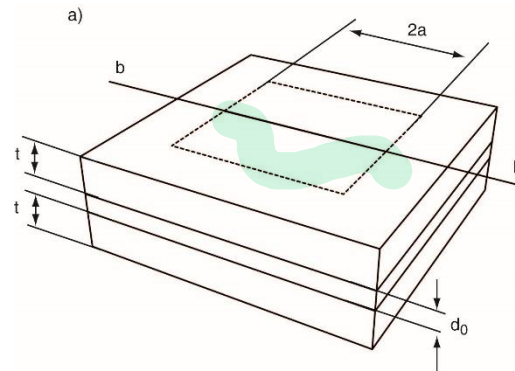
Bending of diaphragm



$$P_{out} = \frac{Et^4}{(1-\nu^2)a^4} \left[ 4.20 \frac{y_0}{t} + 1.58 \frac{y_0^3}{t^3} \right]$$

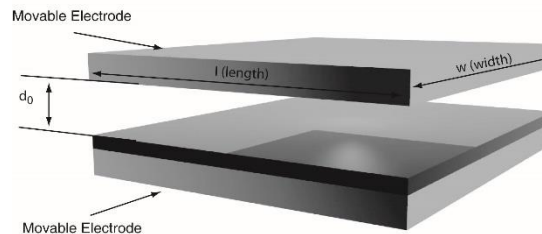


$$y(x, y) = y_0 \left[ \left( \cos\left(\frac{\pi x}{2a}\right) \right) \left( \cos\left(\frac{\pi y}{2a}\right) \right) \right]$$



### Electrostatic domain

### Capacitor



$$C = \epsilon_0 \epsilon_r \frac{wl}{d_0}$$

$$C = \int_0^{2a} \int_0^{2a} \frac{\epsilon_0 \epsilon_r}{d_0 + 2y(x, y)} dy dx$$



# Pressure Sensors – BMP280

Piezo-resistive

Fully CMOS compatible MEMS manufacturing

Hermetic sealing of the cavity

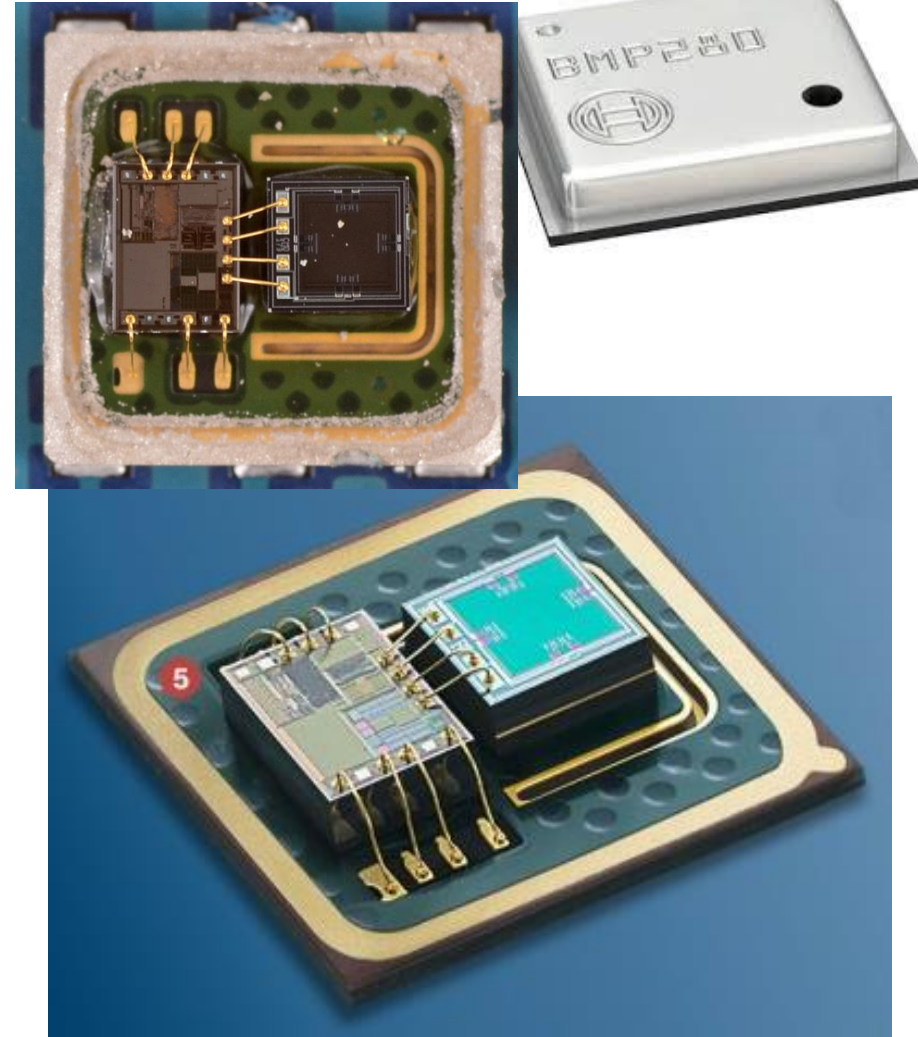


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Parameter	Technical data
Package dimensions	8-Pin LGA with metal 2.0 x 2.5 x 0.95 mm <sup>2</sup>
Operation range (full accuracy)	Pressure: 300...1100 hPa Temperature: -40...85°C
Supply voltage VDDIO Supply voltage VDD	1.2 ... 3.6 V 1.71 ... 3.6 V
Interface	I <sup>2</sup> C and SPI
Average current consumption (1Hz data refresh rate)	2.74 µA, typical (ultra-low power mode)
Average current consumption in sleep mode	0.1 µA
Average measurement time	5.5 msec (ultra-low power preset)
Resolution of data	Pressure: 0.01 hPa (< 10 cm) Temperature: 0.1°C
Absolute accuracy p=950 ... 1050hPa (T=0 ... +40°C)	~ ±1 hPa
Relative accuracy pressure p=950 ... 1050hPa (+25°C)	± 0.12 hPa (typical) equivalent to ±1 m
Temperature coefficient offset (+25°...+40°C @900hPa)	1.5 Pa/K equiv. to 12.6 cm/K

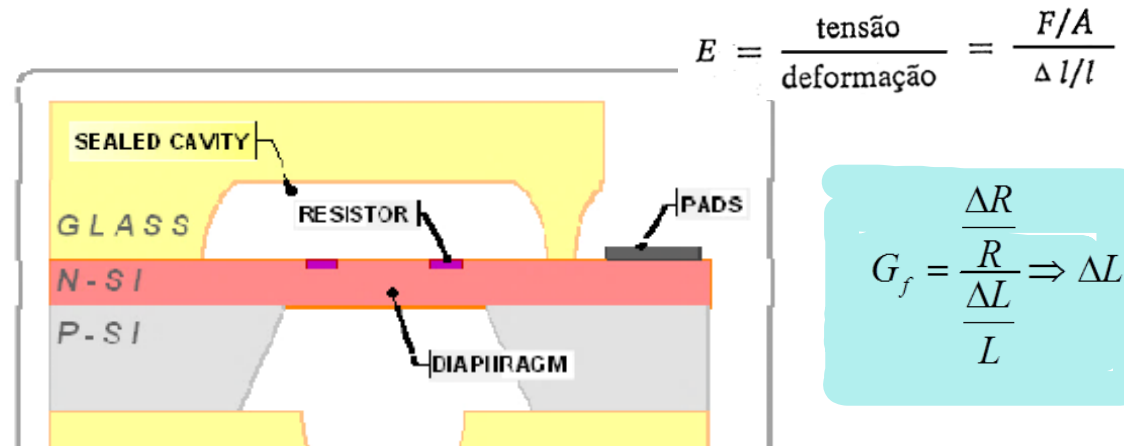
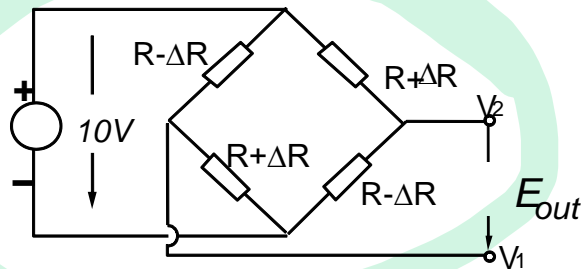
1 hectopascal = 1 millibar

1 bar = 100 kilopascal



Quatro extensômetros são utilizados numa membrana (módulo de elasticidade (Young) de  $1 \times 10^7 \text{ N/m}^2$ ) para implementar um sensor de pressão. O extensômetro tem uma resistência nominal (não deformado) de  $240\Omega$ , um fator de Gauge de 2.0 e um coeficiente de variação com a temperatura de  $0.003\Omega/\Omega/^\circ\text{C}$ . A ponte de Wheatstone tem 4 extensômetros ativos ( $R+\Delta R$  e  $R-\Delta R$ ).

### EXERCÍCIO

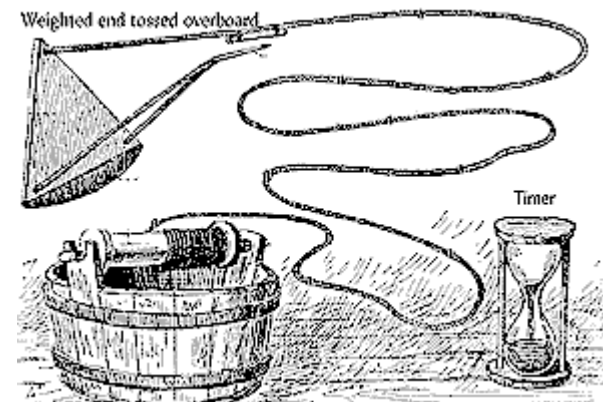


- Qual a alteração na resistência do extensômetro para uma pressão de 1 atm? ( $4.8\Omega$ )
- Qual a tensão na saída da ponte de Wheatstone para uma pressão de 1 atm? (200mV)
- Qual a sensibilidade do sensor de pressão, quando alimentado a 10V? (200mV/atm)
- Qual a tensão na saída da ponte de Wheatstone para uma carga de 1 atm, se a temperatura aumentar  $10^\circ\text{C}$  em todos os extensômetros? (200mV)
- Qual o maior erro na tensão de saída da ponte de Wheatstone, se um dos extensômetros estiver  $1^\circ\text{C}$  acima dos restantes? (7mV?)

## 2. Flow Sensors



Sensores de  
Fluídos



# Flow Sensors

## ■ Introduction

- First micromachined flow sensors date back to the seventies.
- A fluid flow can be either a gas flow or a liquid flow and the measurands can be either mass moved (weight per second), distance moved (meters per second) or the volume moved (volume per second).
- Microfabrication offers:
  - *High resolution.*
  - *Fast time response.*
  - *Integrated signal processing.*
  - *Low-cost.*
- Applications
  - *Automotive – Fuel injection systems (MAF), climate control.*
  - *Civil engineering – Wind forces on buildings.*
  - *Medicine.*
  - *Process Industry.*
  - *Water metering*

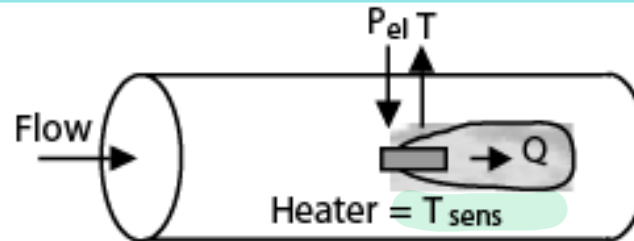


# Flow Sensors

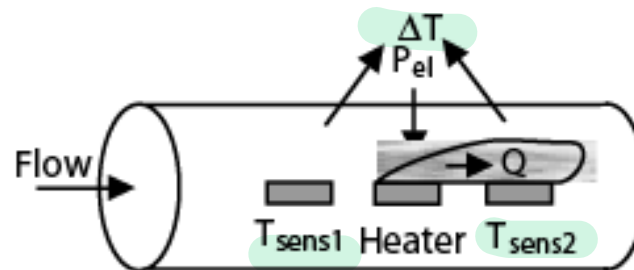
## Thermal flow sensors

- Many micro-flow sensors work in the thermal domain.
- Thermal flow sensors have been classified into three basic categories:

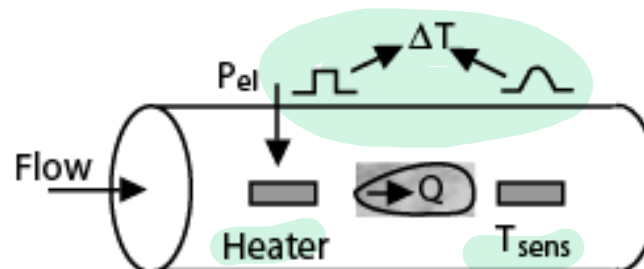
- Anemometers.



- Calorimetric flow sensors.



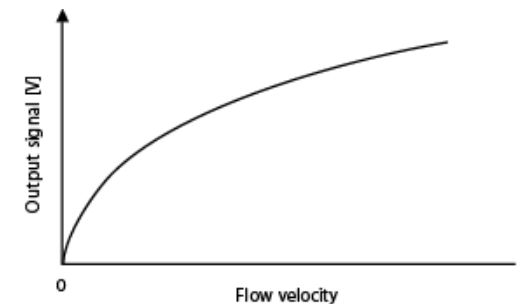
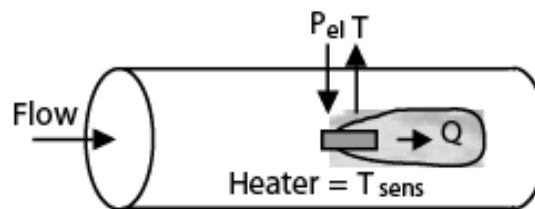
- Time of flight sensors.



# Flow Sensors

## ■ Anemometers (Heat Loss)

- Consist of a element that is heated, and the influence of the fluid flow on the element is measured.
- They are operated in:
  - *Constant power mode* – Heat is dissipated from the resistor into the fluid flow, and the resulting temperature of the resistor is a measure of that flow.
  - *Constant temperature mode* – The temperature of the heater is directly measured and kept constant above ambient temperature. The electrical power needed to maintain a constant temperature is a measure of the flow.
- Fast responses.
- Not bidirectional.
- Limited power range.
- Sensitive to contamination.
- Made very thin to have a fast response.

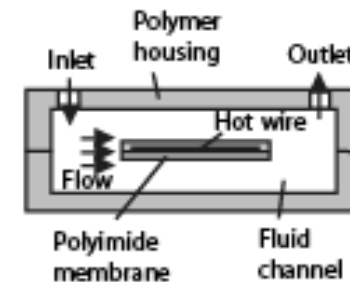
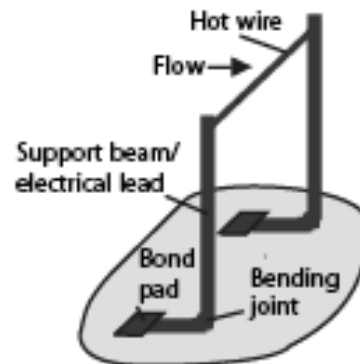
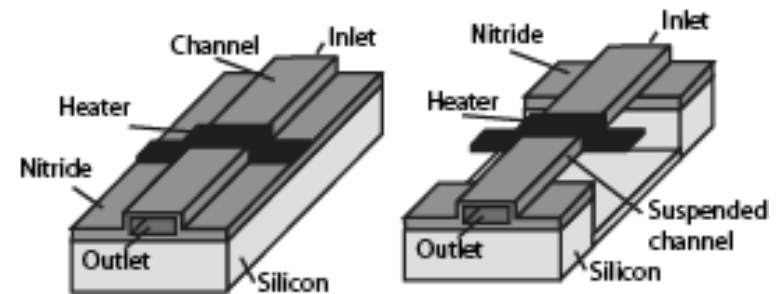
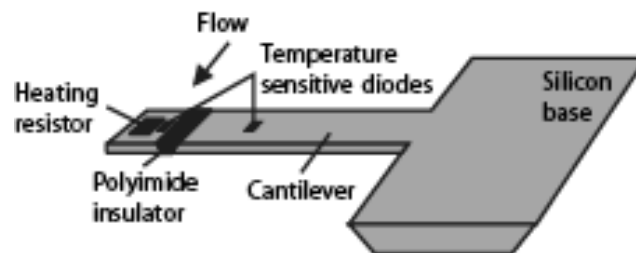


Curve of an anemometer flow sensor operated in constant power mode

# Flow Sensors

## ■ Anemometers (Heat Loss)

- Examples

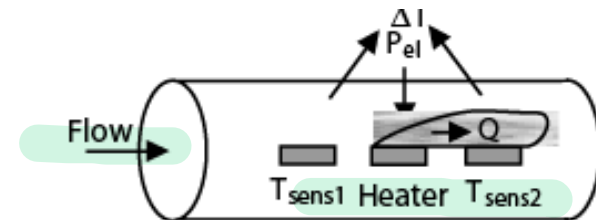
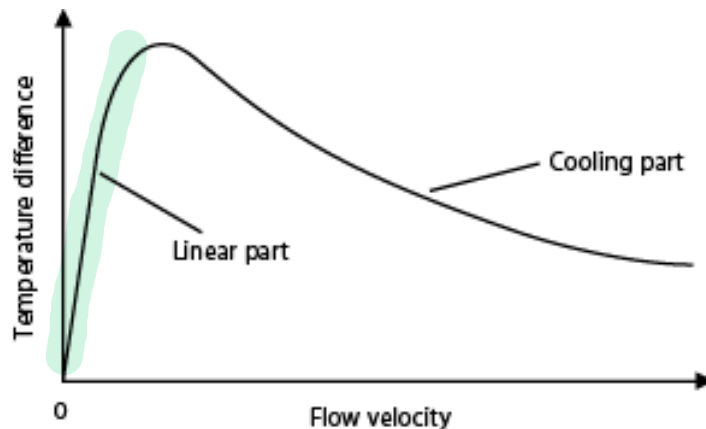


Source: *MEMS Mechanical Sensors*

# Flow Sensors

## ■ Calorimetric flow sensors

- This type of sensors use a heating element with temperature sensing elements up- and downstream:
  - The upstream sensor is cooled by the flow and the downstream sensor is heated due to the heat transport from the heater in the flow direction.
  - The amount of heat measured is proportional to the flow rate.
  - The output signal is the difference in temperature between the up- and downstream sensors.
- Needs calibration for each fluid.

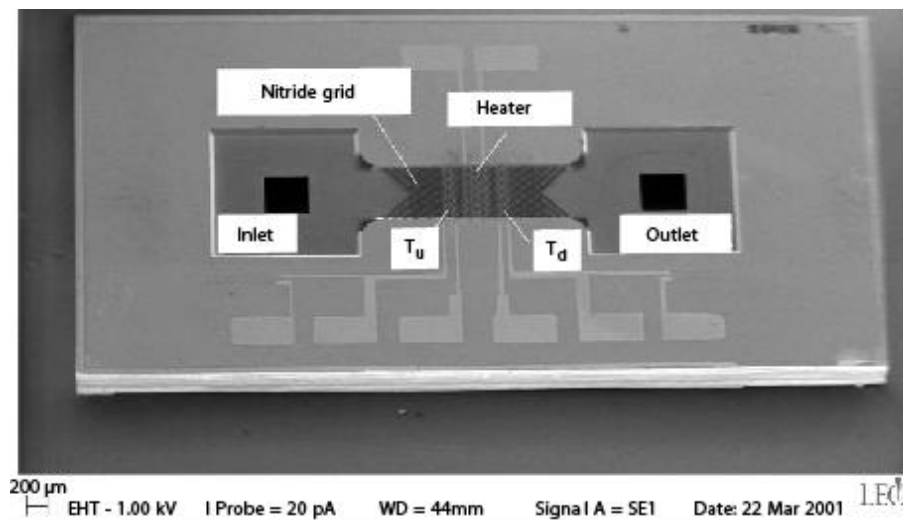
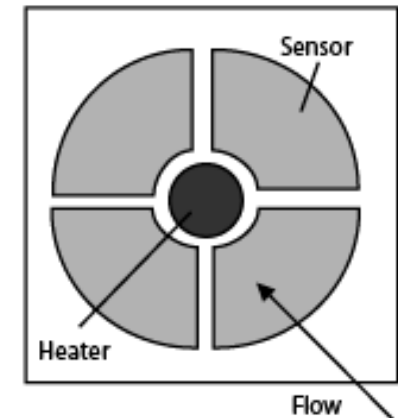
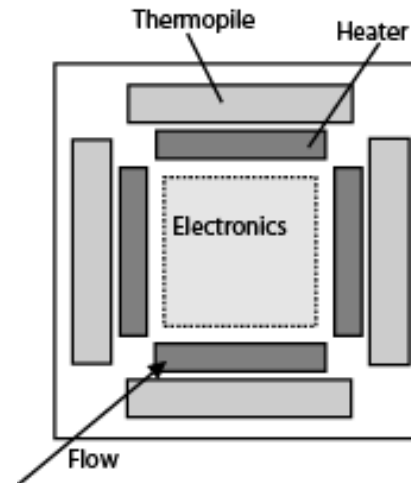


Curve of an calorimetric flow sensor operated in constant power mode

Measurements can be taken at linear part

# Flow Sensors

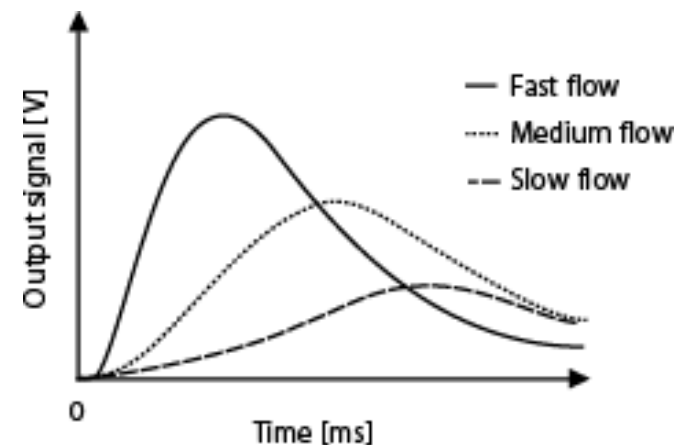
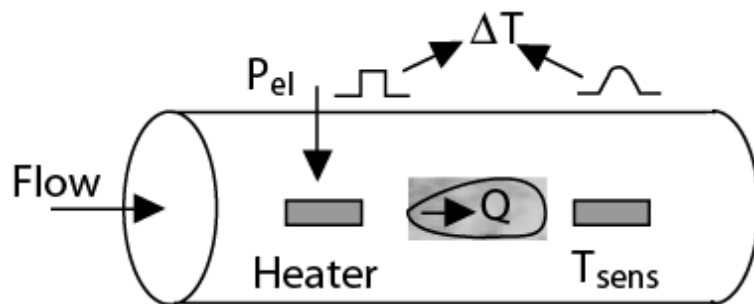
- Calorimetric flow sensors
  - Examples



# Flow Sensors

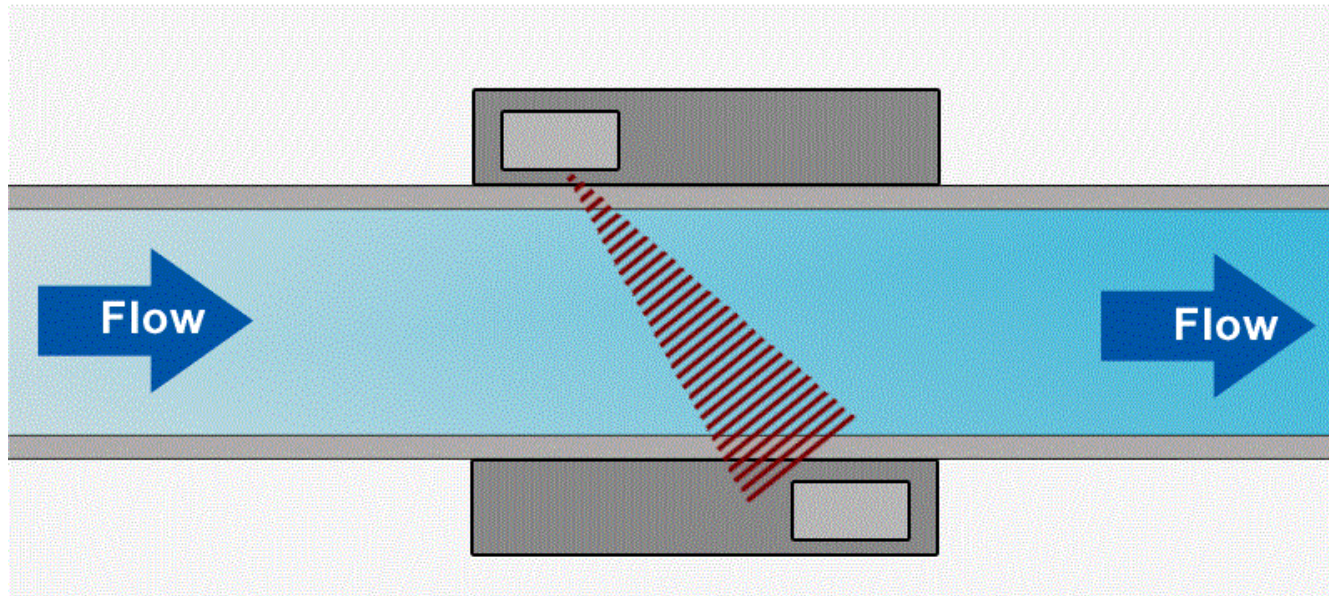
## Time of flight sensors

- The heater is continually pulsed with a certain amount of electrical energy. The heat pulse is carried away from the heater by the flowing fluid, and the temperature sensor is used to measure the time delay between heat source and heat detection.
- Tolerant to changes in ambient temperature.
- Measurement range set by the distance between heat source and heat detection.



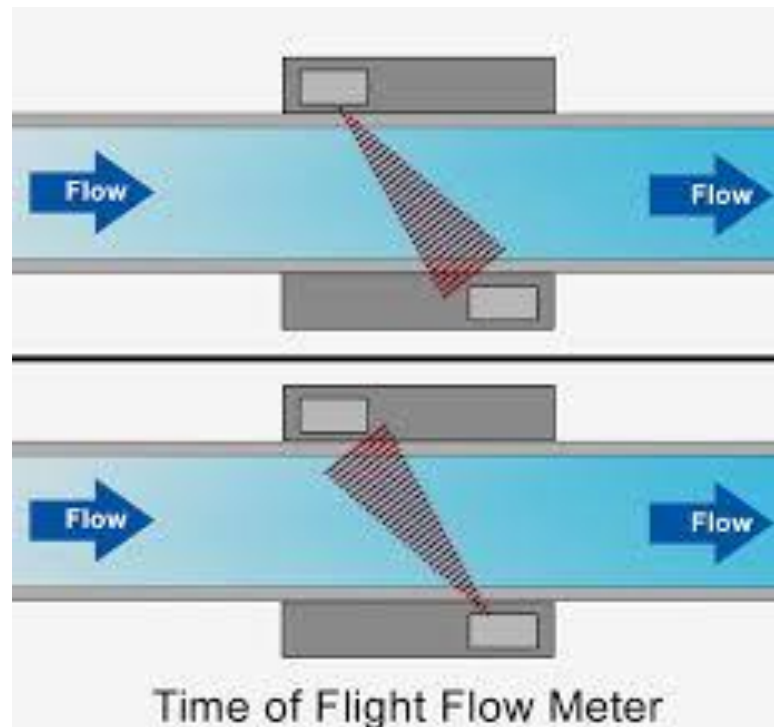
Typical measurement curve of a thermal of flight flow sensor

# Ultrasonic time of flight flow sensor



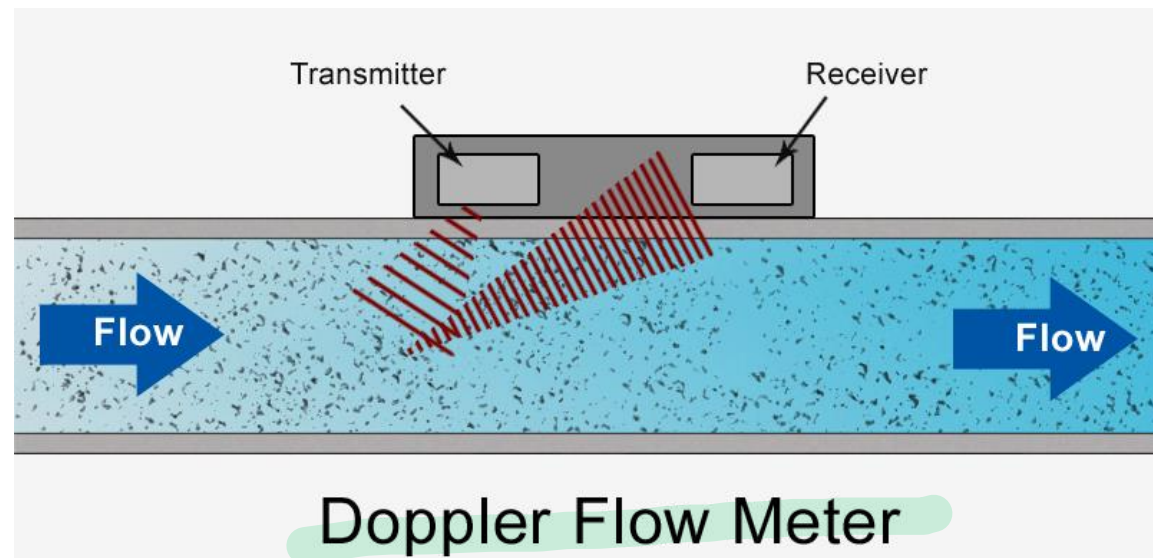


# Ultrasonic time of flight flow sensor





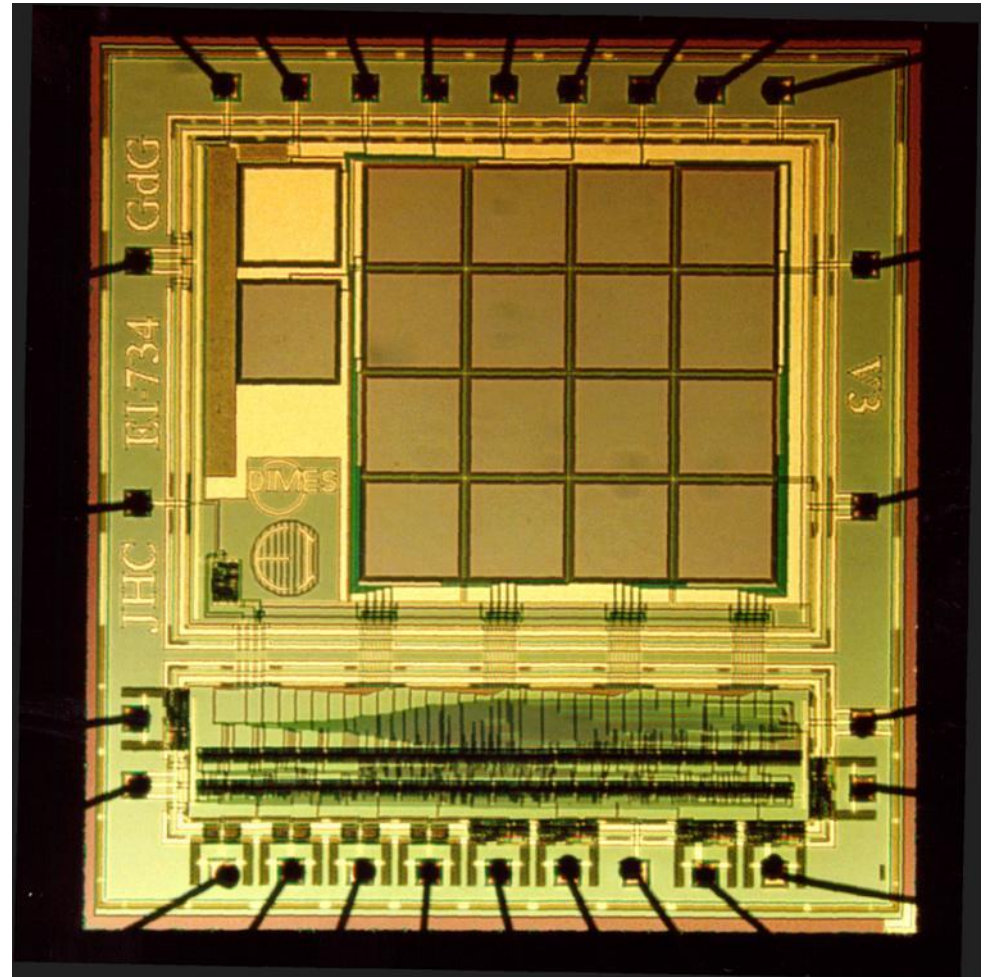
# Ultrasonic Doppler flow sensor



### 3. Sensores Óticos

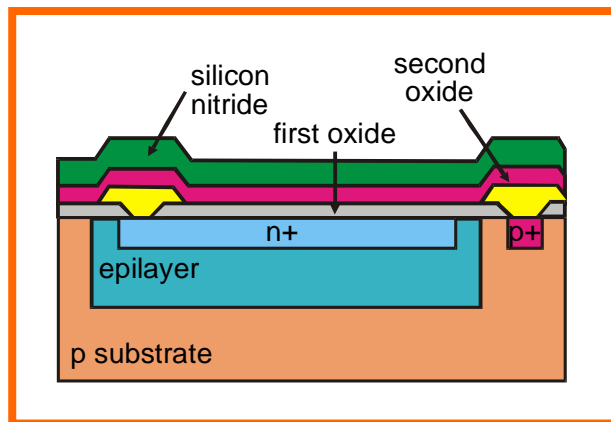


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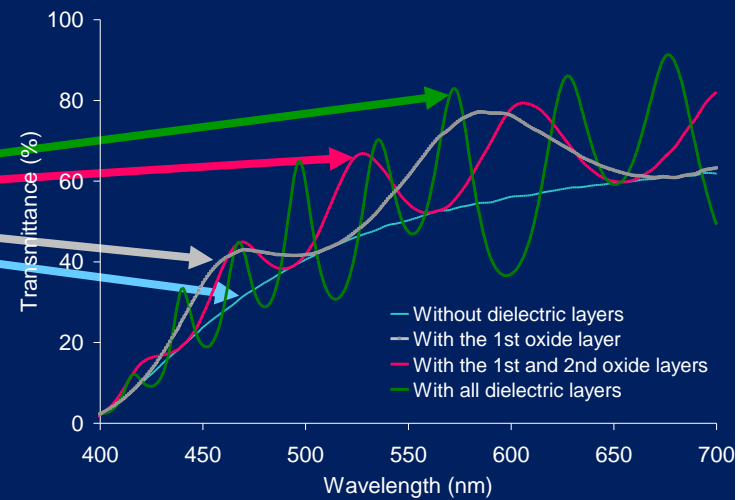
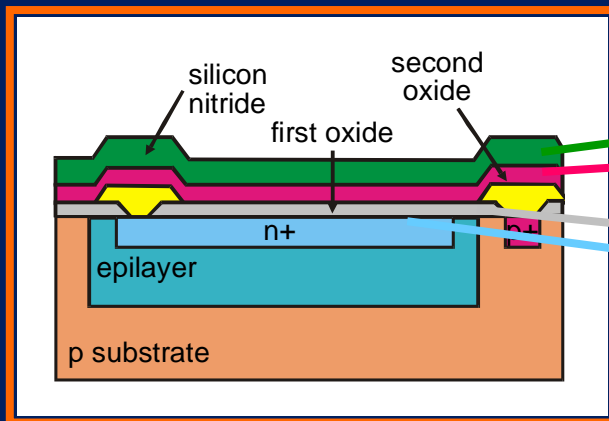
## Fotodetector



- Photodiode n+ / p-epilayer
- CMOS standard process
- Provides the best possible quantum efficiency in the desired spectral range

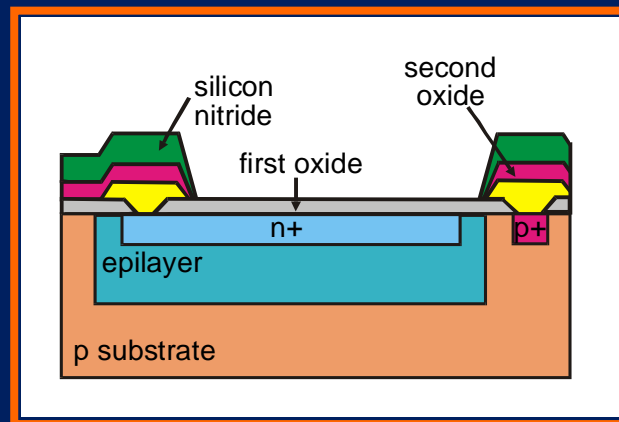
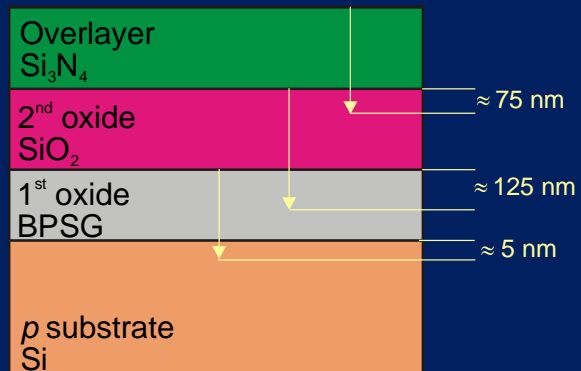
# Photodetector

## Photodiode



# Photodetector

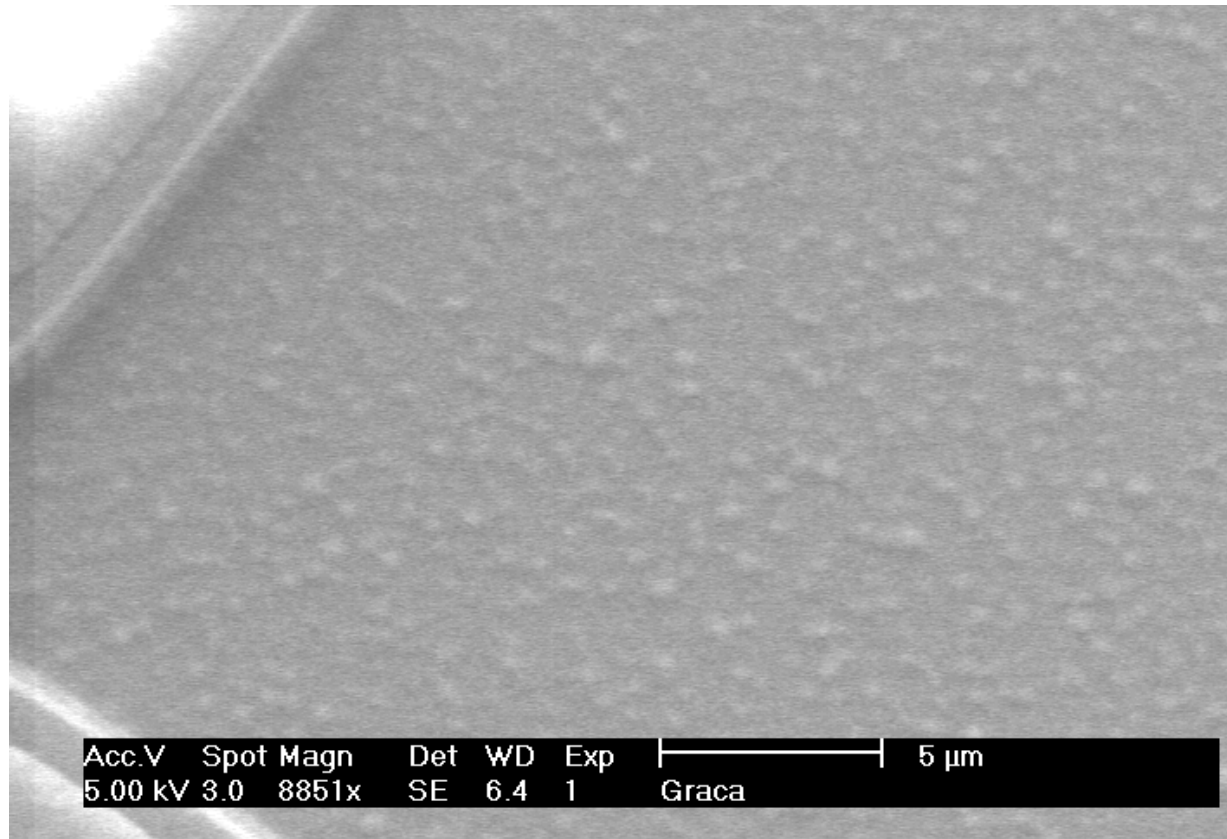
## *Etching*



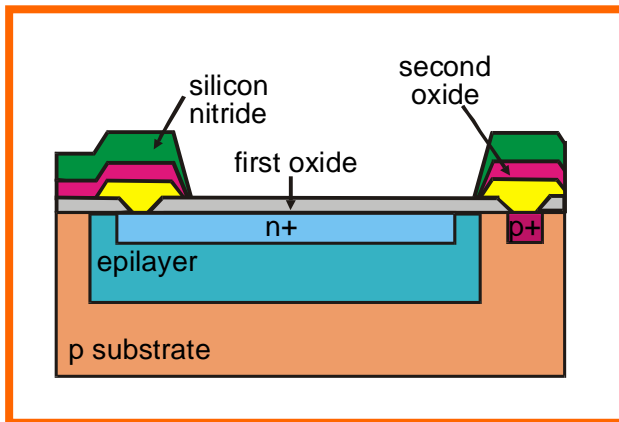
# Photodetector



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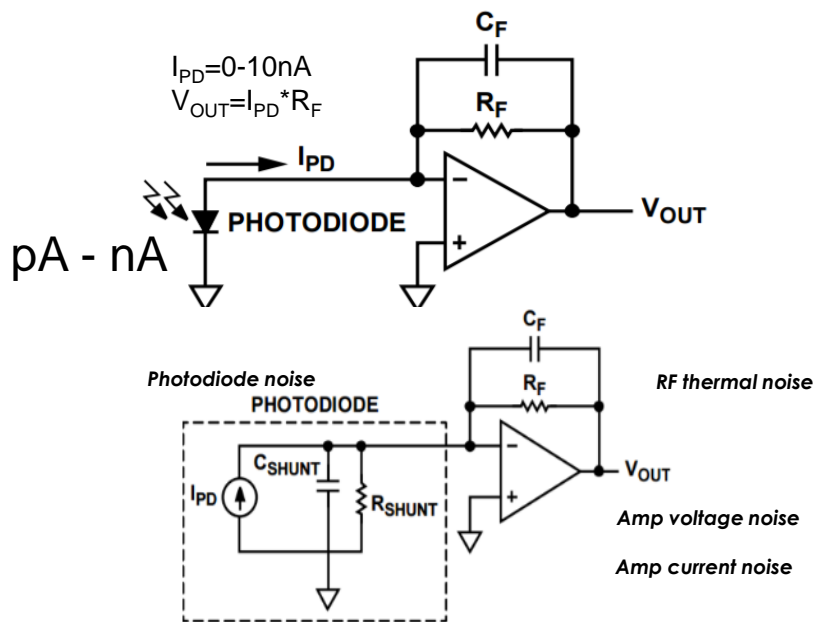


## Photodiode



A light-to-frequency converter is integrated with the photodiodes to convert the photocurrent into a digital signal

# Electronics - Detection




Light Detection is based in a typical transimpedance amplifier optimized for low noise operation

Noise Source	RTO Noise Equation
$R_F$	$\sqrt{4 k T R_F}$
$R_{SHUNT}$ (Photodiode)	$\frac{R_F}{R_{SHUNT}} \sqrt{4 k T R_{SHUNT}}$
Amp Current Noise	$I_N R_F$
Amp Voltage Noise	$V_N \times (1 + \frac{C_{SHUNT}}{C_F})$




# Photodiode Circuit Design Wizard

<https://tools.analog.com/en/photodiode/>

 **ANALOG DEVICES**  
AHEAD OF WHAT'S POSSIBLE™

Photodiode Circuit Design Wizard

myAnalog  Tools

Load Design Save Help English ▾

**Photodiode** Circuit Design Next Steps

**Photodiode Bias**

☐ Reverse Voltage ( $V_R$ ) 0 V

☐ positive

☒ negative

**Photodiode Specs**

☐ Capacitance ( $C_D$ ) at  $V_R = 0$  V 100p F

☐ Shunt Resistance ( $R_{SH}$ ) 1G  $\Omega$

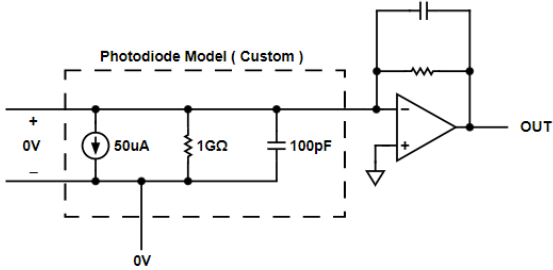
☐ Peak Current ( $I_P$ ) 50u A

or

Select Photodiode from Library

**PHOTODIODE** **TRANSIMPEDANCE AMPLIFIER**

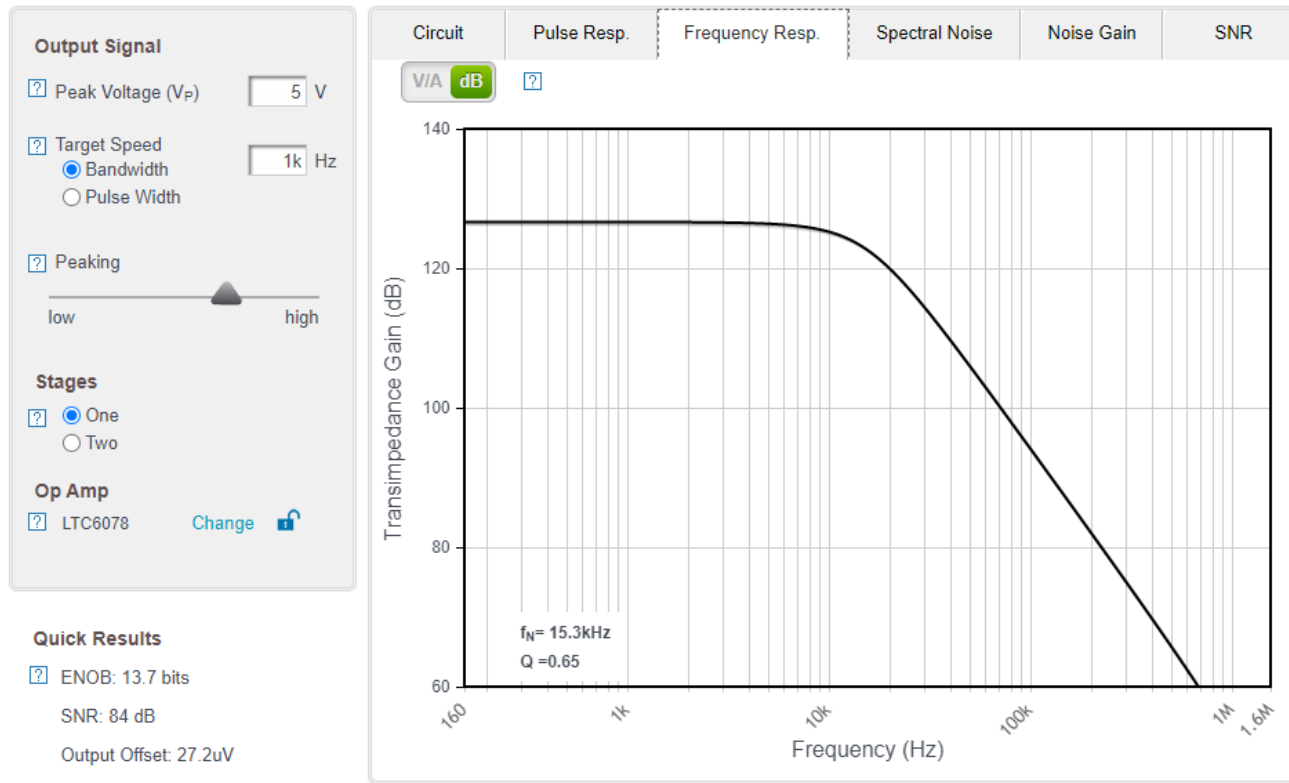
Photodiode Model ( Custom )



Seleção das características do fotodiodo e da saída do circuito

# Photodiode Circuit Design Wizard

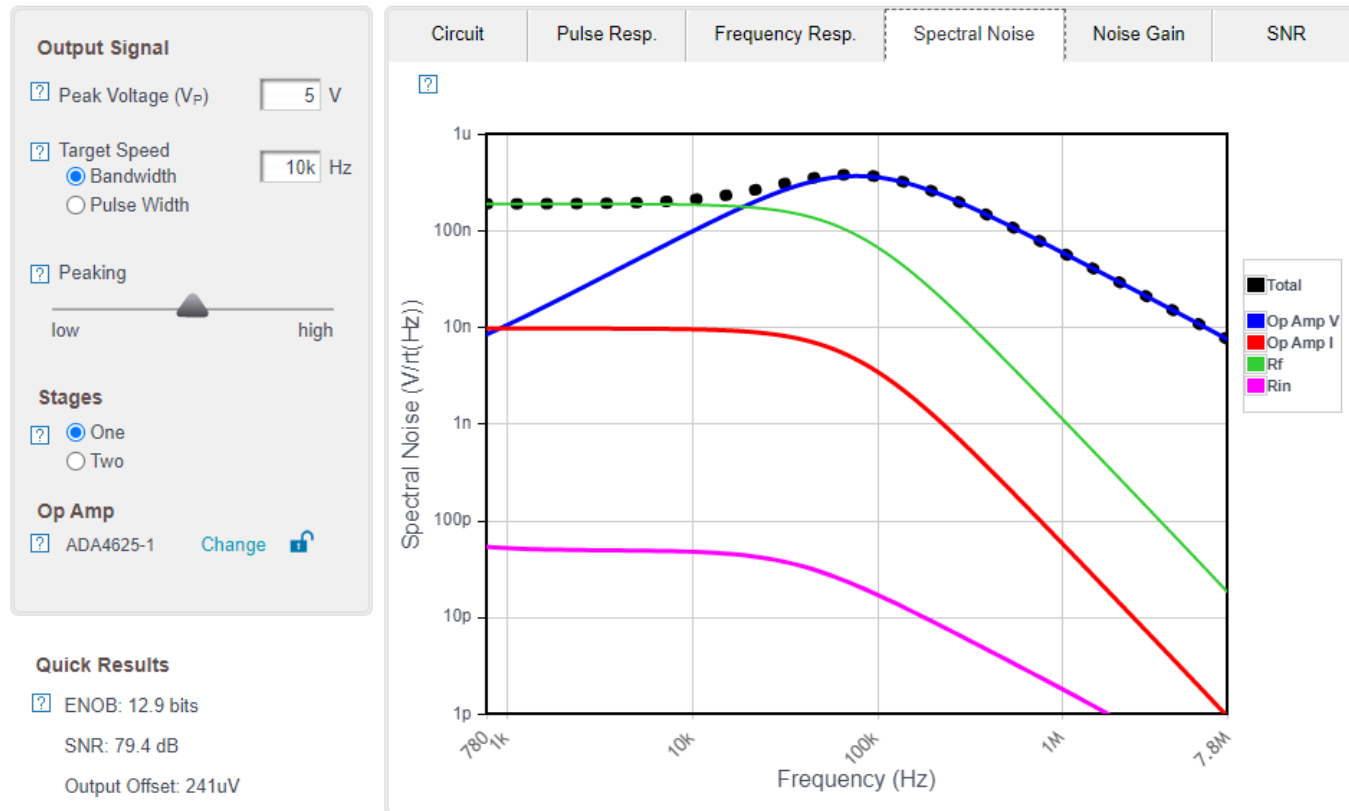
<https://tools.analog.com/en/photodiode/>



Resposta em frequência (ganho é V/A)  
O peaking permite ajustar o Q (fator qualidade)

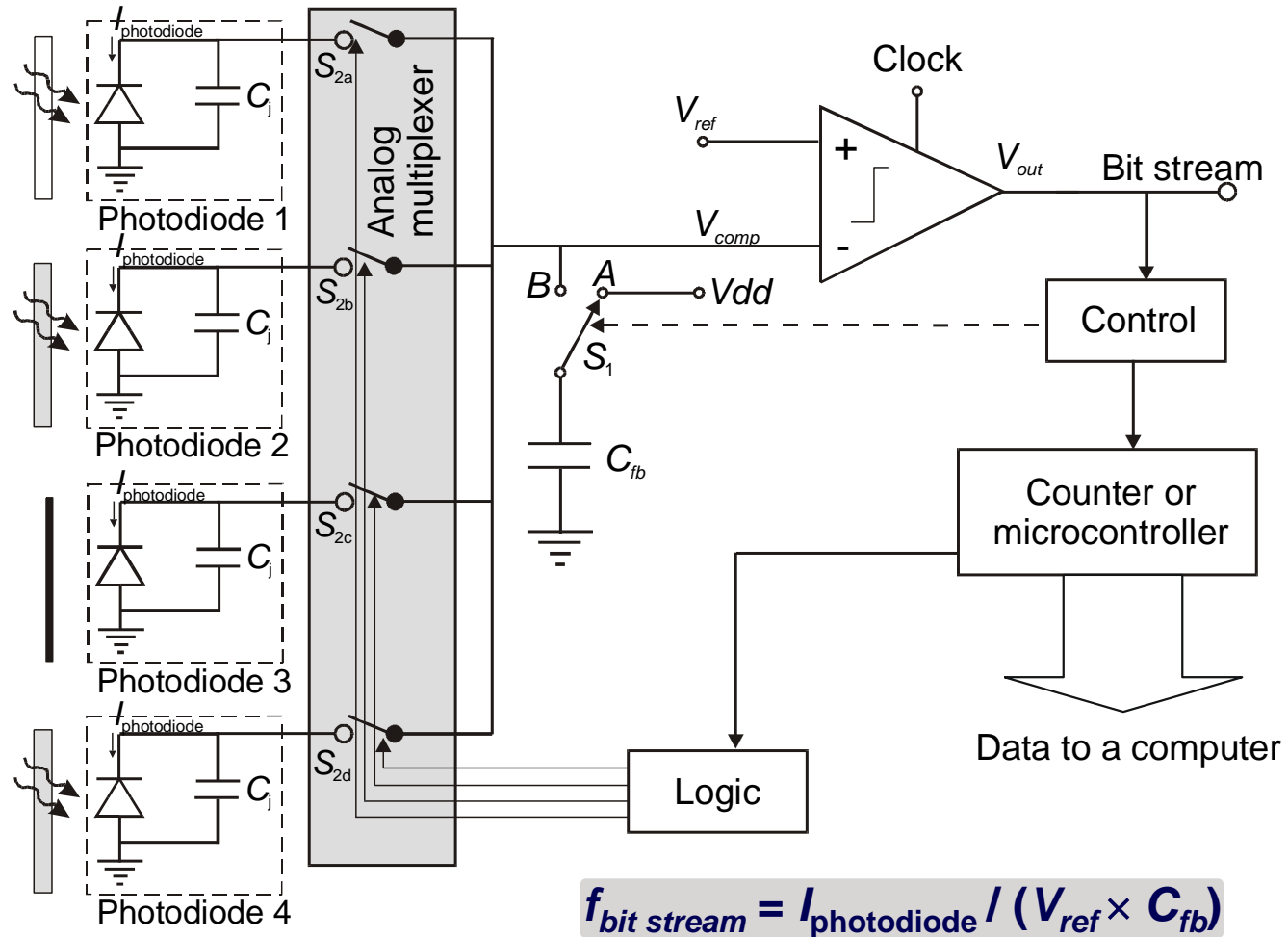
# Photodiode Circuit Design Wizard

<https://tools.analog.com/en/photodiode/>



Ruido em função da frequência.  
ENOB; SNR; Offset

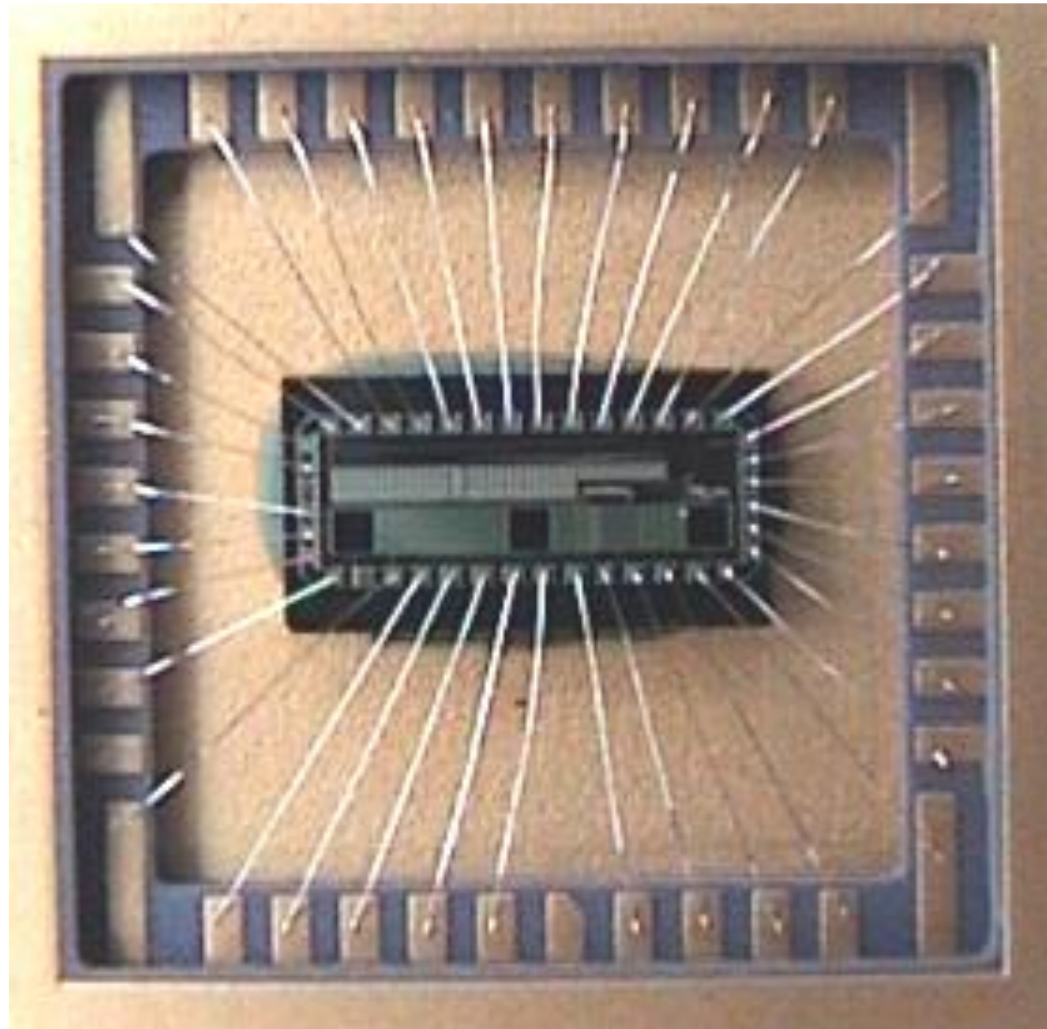
# ELECTRÓNICA de LEITURA



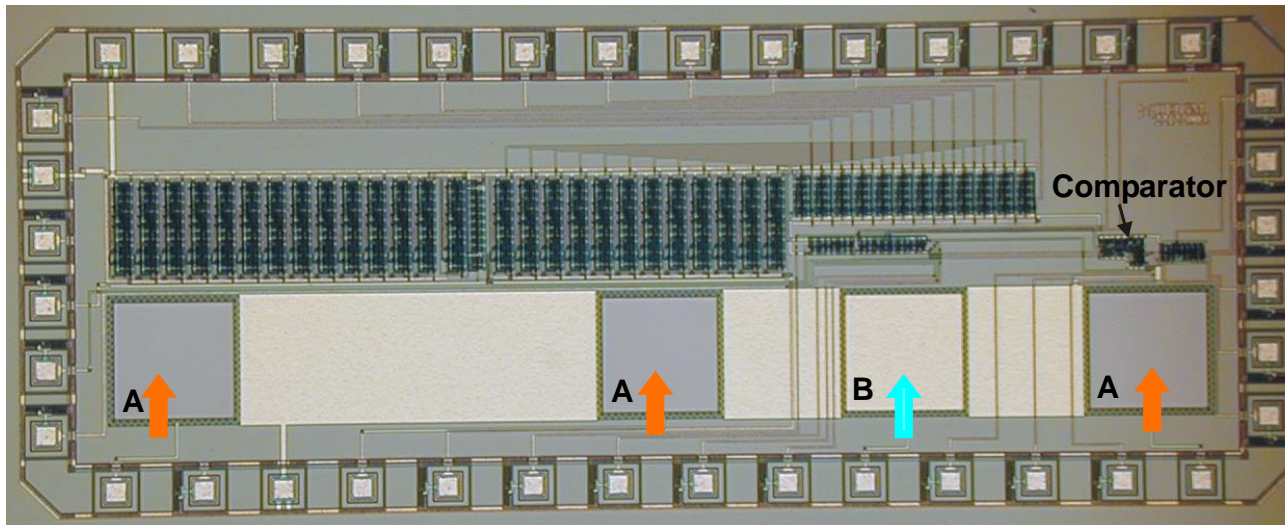
# O SISTEMA de DETECÇÃO e LEITURA



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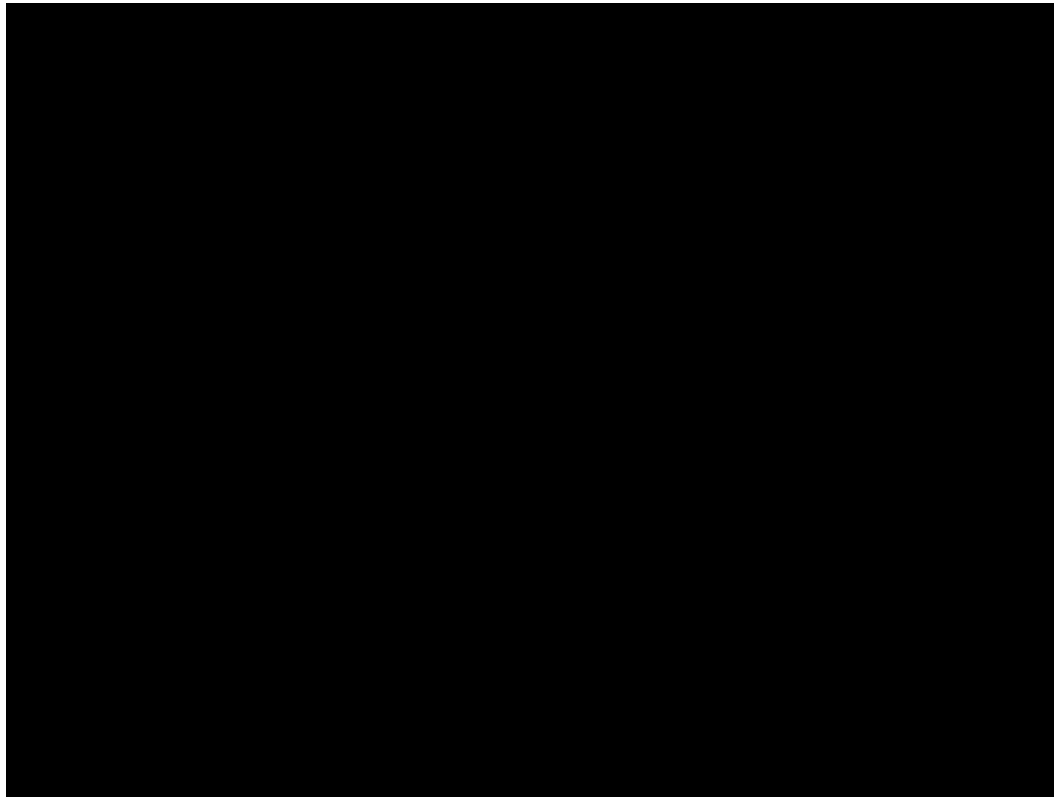


# O SISTEMA de DETECÇÃO e LEITURA



- 1.6  $\mu\text{m}$  n-well CMOS standard process, with double-metal and single-polysilicon
- Each optical channel area is  $500 \mu\text{m} \times 500 \mu\text{m}$

## Conversor luz - frequência

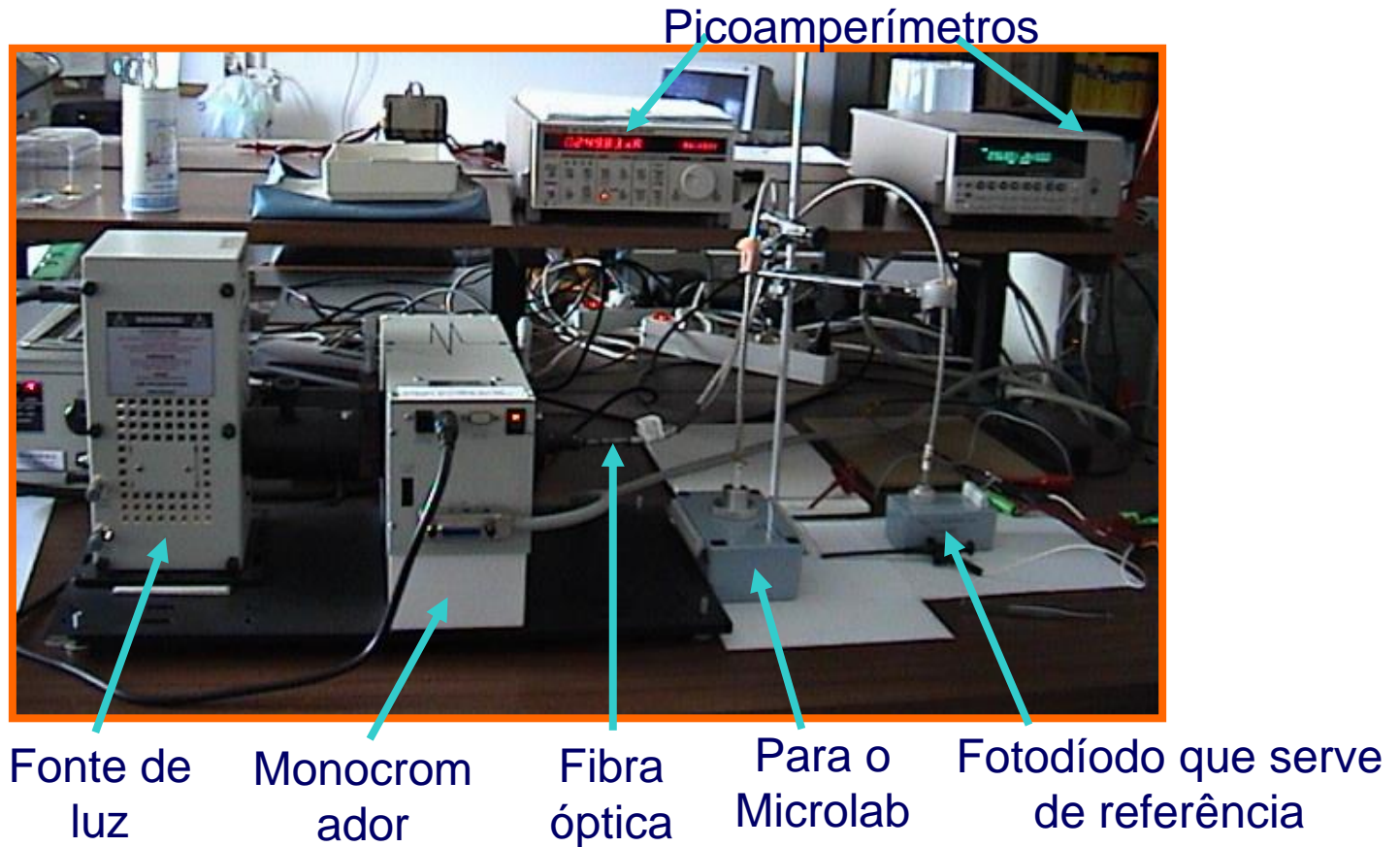


Diminuição da  
intensidade da  
luz

- A frequência da saída do conversor é diretamente proporcional à intensidade da luz



# INSTALAÇÃO EXPERIMENTAL

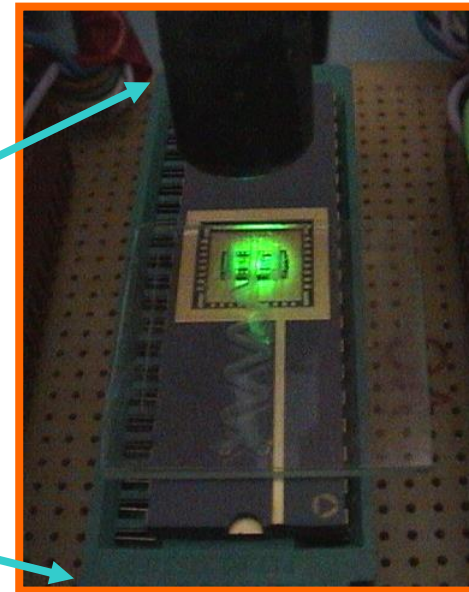
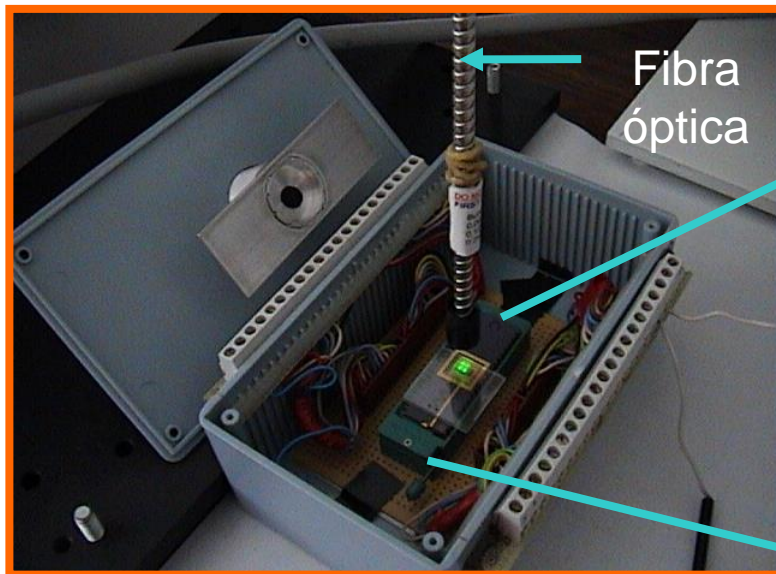




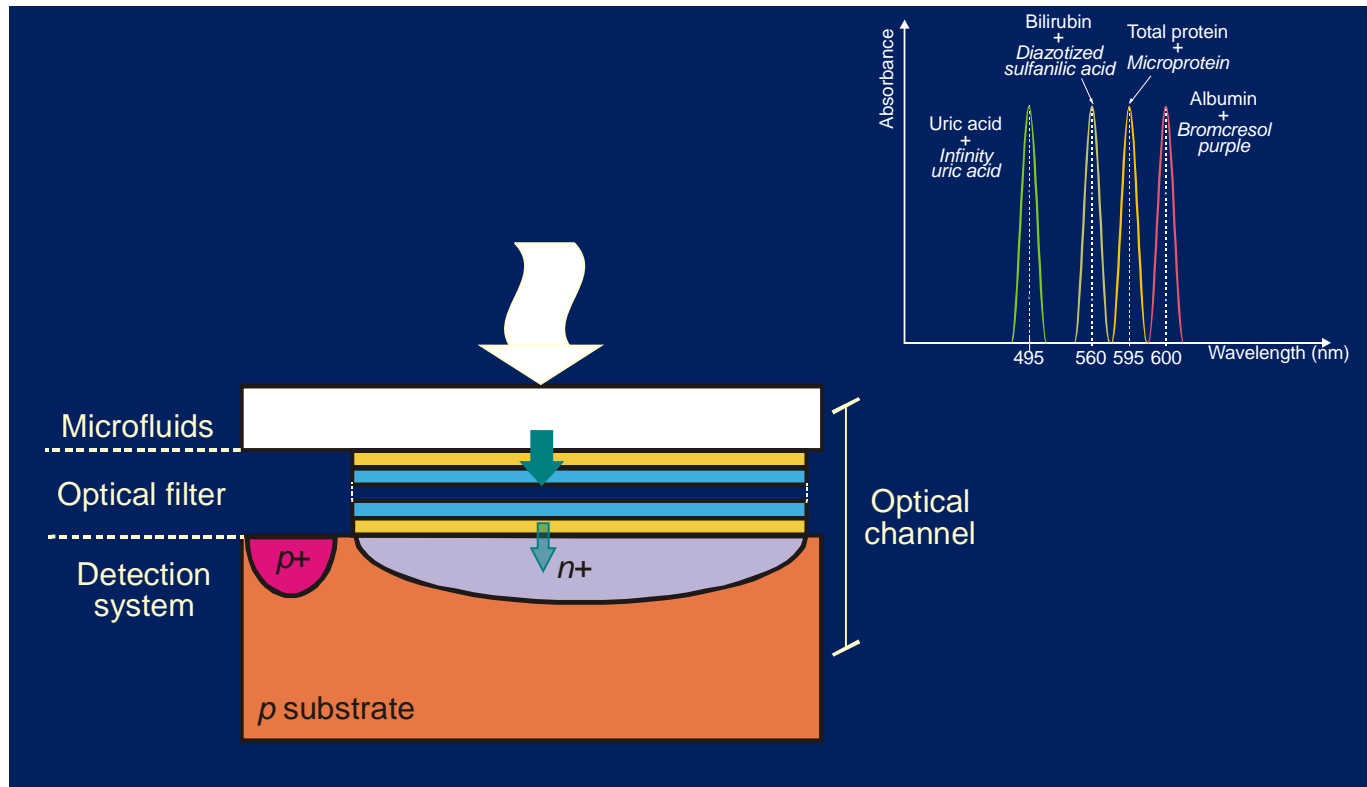
# INSTALAÇÃO EXPERIMENTAL



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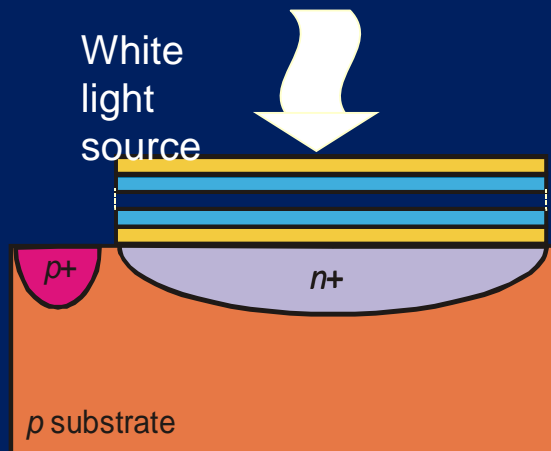


# Optical detection system



# Optical detection system

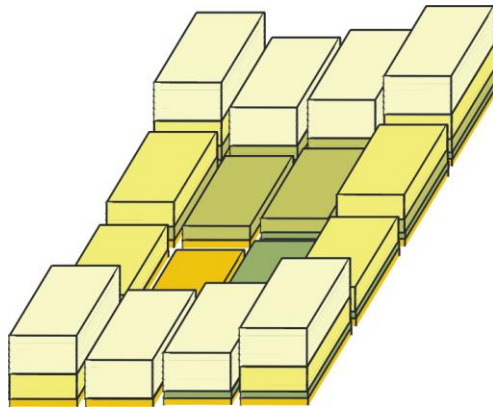
## Portability



- Structurally optimized for:
  - high transmittance
  - high selectivity (low **FWHM**)
- FP thin-films optical resonators with dielectric mirrors ( $\text{TiO}_2$  and  $\text{SiO}_2$ )
- High reflectivity with low absorption losses

Layers post-processed on top of the photodiodes by Ion Beam Deposition (IBD)

# Optical detection system



- Each of the Fabry-Perot cavities is tuned to transmit in different spectral band

